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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE
ATTY. DOCKET NO. 71493-1041

In re Patent Application of JOHN WHITE

Serial No. 10/025,866

Group Art Unit: 2881

Filed: December 26, 2001

Examiner:



For: ENHANCED LINK OPERATION OF DIRECTLY MODULATED LASERS USING GAIN-
COUPLED GRATINGS

INFORMATION DISCLOSURE STATEMENT

This Information Disclosure Statement is being filed in the manner prescribed by 37 CFR 1.97(b)

- (d) to satisfy the duty under 37 CFR 1.56 to disclose to the Office information, known to individuals associated with the filing and prosecution of the subject application, which is material to the examination of the application.

In accordance with 37 CFR 1.97(g) and (h), this statement is not to be construed as a representation that a search has been made or an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

This information disclosure statement is being filed within three months of the filing date of a national application, within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first official action on the merits and therefore applicant respectfully requests consideration under 37 CFR 1.97(b).

In compliance with 37 CFR 1.98(a)(1), a list of all patents, publications or other information submitted for consideration by the Office is hereby provided by way of the attached Form PTO 1449.

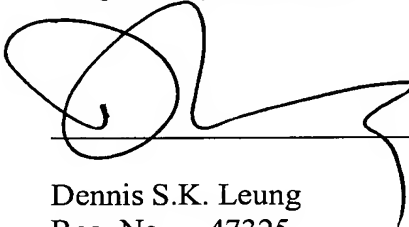
In compliance with 37 CFR 1.98(a)(2), also enclosed is a legible copy of:

- i) each United States and foreign patent;
- ii) each publication or that portion which caused it to be listed; and
- iii) all other information or that portion which caused it to be listed, excluding any copies of a United States patent application.

It is respectfully requested that the information be expressly considered by the Examiner and that the references be made of record and appear among the "References Cited" on any patent to issue therefrom.

The Patent Office is hereby authorized to charge any deficiency, or credit any overpayment in fees to Deposit Account Number 19-2550.

Respectfully submitted,

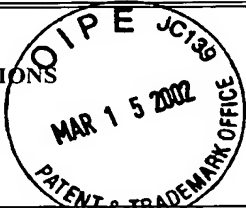


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Dated: March 14, 2002

Encls.: Form PTO-1449
All references listed on Form PTO-1449
Acknowledgement card

Form PTO-1449 (Modified) LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		Atty. Docket No. 71493-1041	Serial No. 10/025,866
		Applicant John White	
		Filing Date December 26, 2001	Group 2881

REFERENCE DESIGNATION U.S. PATENT DOCUMENTS

EXAM. INIT.	DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FIL. DATE IF APPROPRIATE
AA						

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS	TRANSLATION	
						YES	NO
AB							

OTHER ART (including Author, Title, Date, Pertinent Pages, Etc.)

AC	Zah Chung-En et al: "High-Performance Uncooled 1.3μm Al _x Ga _{1-x} As/InP Strained-Layer Quantum-Well Lasers for Subscriber Loop Applications", IEEE Journal of Quantum Electronics, February 1994, vol. 30, no. 2, pages 511-523
AD	Lowery Arthur J. et al: "Performance Comparison of Gain-Coupled and Index-Coupled DFB Semiconductor Lasers", IEEE Journal of Quantum Electronics, September 1994, vol. 30, no. 9, pages 2051-2063
AE	Lu Hanh et al: "Dynamic Properties of Partly Gain-Coupled 1.55-μm DFB Lasers", IEEE Journal of Quantum Electronics, August 1995, vol. 31, no. 8, pages 1443-1450
AF	Lu Hanh et al: "Single-Mode Operation Over a Wide Temperature Range in 1.3μm InGaAsP/InP Distributed Feedback Lasers", Journal of Lightwave Technology, May 1996, vol. 14, no. 5, pages 851-859
AG	Chen Jianyao et al: "Transient Side-Mode Suppression in Gain-Coupled DFB Lasers", IEEE Journal of Quantum Electronics, January 1998, vol. 34, no. 1, pages 113-119
AH	Hong J. et al: "Strongly Gain-Coupled (SGC) Coolerless (-40°C ~ +85°C) MQW DFB Lasers", IEEE Journal of Selected Topics in Quantum Electronics, May/June 1999, vol. 5, no. 3, pages 442-448
AI	Massara A.B. et al: "Ridge waveguide InGaAsP lasers with uncooled 10Gbit/s operation at 70°C", Electronics Letters, September 16, 1999, vol. 35, no. 19, pages 1646-1647
AJ	Champagne A. et al: "Global and Local Effects in Gain-Coupled Multiple-Quantum-Well DFB Lasers". IEEE Journal of Quantum Electronics, October 1999, vol. 35, no. 10, pages 1390-1401
AK	Springthorpe A.J. et al: "Strained 1.3μm MQW AlGaInAs lasers grown by digital alloy MBE", Electronics Letters, June 8, 2000, vol. 36, no. 12, pages 1031-1032
AL	Ebberg A. et al: "10 Gbit/s transmission using directly modulated uncooled MQW ridge waveguide DFB lasers in TO package", Electronics Letters, August 17, 2000, vol. 36, no. 17, pages 1476-1477
AM	White J.K. et al: "85°C Investigation of Uncooled 10-Gb/s Directly Modulated InGaAsP RWG GC-DFB Lasers", IEEE Photonics Technology Letters, August 2001, vol. 13, no. 8, pages 773-775
AN	Yang S. et al: "Enhanced Performance of Uncooled Strongly-Gain-Coupled MQW DFB Lasers in 10Gb/s Link Applications", paper presented at European Conference for Optical Communications, Fall 2001

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.